Power MOSFET -12V, 70mΩ, -3A, Single P-Channel

This Power MOSFET is produced using ON Semiconductor's trench technology, which is specifically designed to minimize gate charge and low on resistance. This device is suitable for applications with low gate charge driving or low on resistance requirements.

Features

- Low On-Resistance
- 1.8V drive
- Pb-Free and RoHS compliance
- Halogen Free compliance: CPH3348-TL-W

Typical Applications

- Load Switch
- DC/DC Converter

SPECIFICATIONS

ABSOLUTE MAXIMUM RATING at Ta = 25°C (Note 1, 2)

Parameter	Symbol	Value	Unit
Drain to Source Voltage	VDSS	-12	V
Gate to Source Voltage	VGSS	±10	V
Drain Current (DC)	ID	-3	Α
Drain Current (Pulse) PW ≤ 10µs, duty cycle ≤ 1%	IDP	-12	Α
Power Dissipation When mounted on ceramic substrate (1200mm² × 0.8mm)	PD	1.0	W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-55 to +150	°C

- Note 1: Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.
 - 2 : This product is designed to "ESD immunity<200V*", so please take care when handling.
 - *Machine Model

THERMAL RESISTANCE RATINGS

THERMAE REGISTANCE RATINGS					
Parameter	Symbol	Value	Unit		
Junction to Ambient					
When mounted on ceramic substrate	$R_{\theta JA}$	125	°C/W		
$(1200 \text{mm}^2 \times 0.8 \text{mm})$					

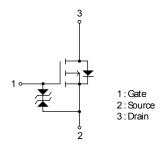


ON Semiconductor®

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VDSS	R _{DS} (on) Max	ID Max
	70mΩ@ –4.5V	
-12V	115mΩ@ –2.5V	-3A
	215mΩ@ -1.8V	

ELECTRICAL CONNECTION P-Channel



ORDERING INFORMATION

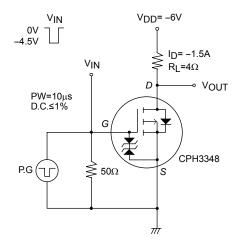
See detailed ordering and shipping information on page 5 of this data sheet.

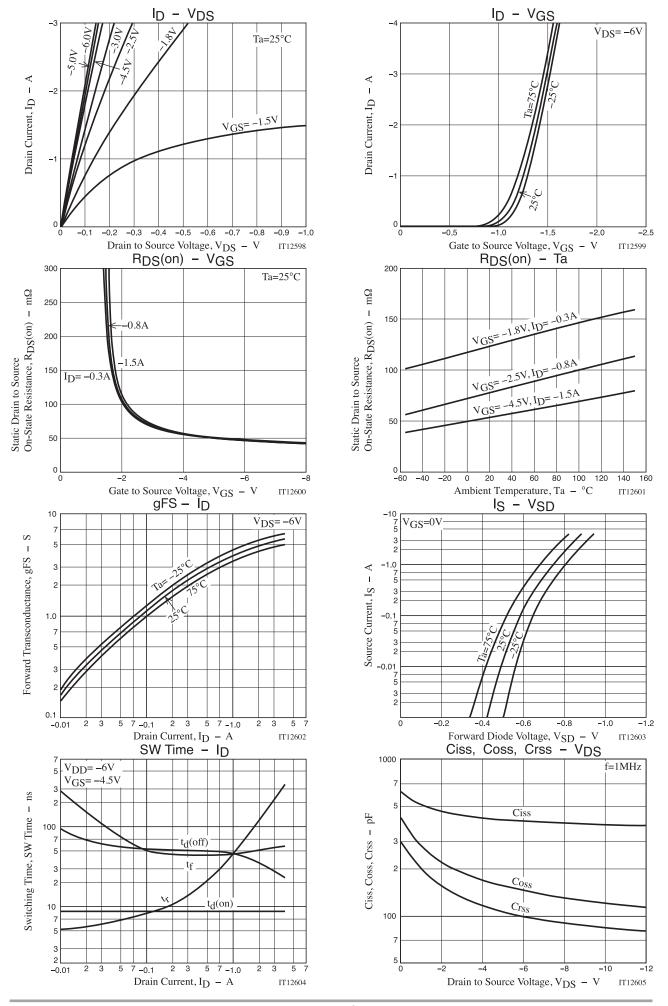
ELECTRICAL CHARACTERISTICS at Ta = 25°C (Note 3)

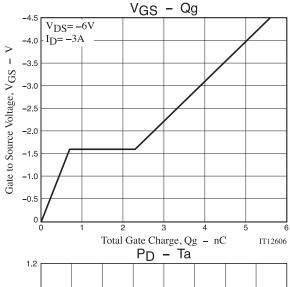
Parameter	Symbol	Conditions	Value			Unit
Farameter	Syllibol	Conditions	min	typ	max	Offic
Drain to Source Breakdown Voltage	V(BR)DSS	I _D =-1mA, V _G S=0V	-12			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =-12V, V _{GS} =0V			-10	μΑ
Gate to Source Leakage Current	IGSS	V _{GS} =±8V, V _{DS} =0V			±10	μА
Gate Threshold Voltage	VGS(th)	V _{DS} =-6V, I _D =-1mA	-0.4		-1.4	V
Forward Transconductance	gFS .	V _{DS} =-6V, I _D =-1.5A		4.3		S
	R _{DS} (on)1	I _D =-1.5A, V _G S=-4.5V		54	70	mΩ
Static Drain to Source On-State Resistance	R _{DS} (on)2	I _D =-0.8A, V _G S=-2.5V		80	115	mΩ
Resistance	R _{DS} (on)3	I _D =-0.3A, V _G S=-1.8V		125	215	mΩ
Input Capacitance	Ciss			405		pF
Output Capacitance	Coss	V _{DS} =–6V, f=1MHz		145		pF
Reverse Transfer Capacitance	Crss			100		pF
Turn-ON Delay Time	t _d (on)			8.8		ns
Rise Time	tr	On a supplied Took Observit		80		ns
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit		41		ns
Fall Time	tf			50		ns
Total Gate Charge	Qg			5.6		nC
Gate to Source Charge	Qgs	V _{DS} =-6V, V _{GS} =-4.5V, I _D =-3A		0.7		nC
Gate to Drain "Miller" Charge	Qgd			1.6		nC
Forward Diode Voltage	V _{SD}	I _S =-3A, V _G S=0V		-0.85	-1.2	V

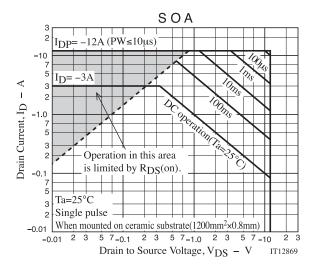
Note 3 : Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

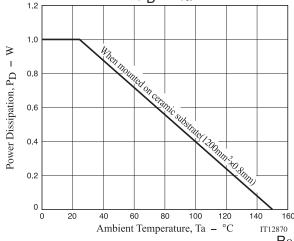
Switching Time Test Circuit

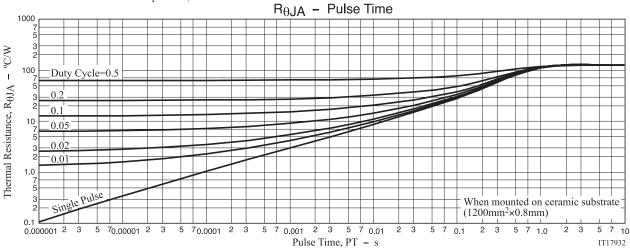






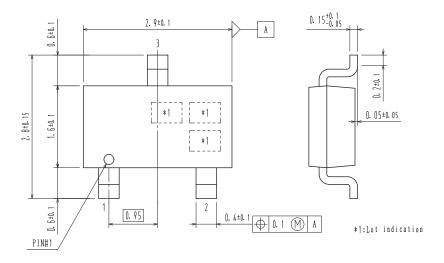






PACKAGE DIMENSIONS

Unit: mm CPH3 CASE 318BA ISSUE O



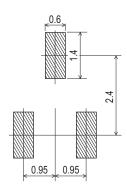
0.0 440.05

1 : Gate

2 : Source

3: Drain

Recommended Soldering Footprint



ORDERING INFORMATION

Device	Marking	Package	Shipping (Qty / Packing)	
CPH3348-TL-E	WE	CPH3 SC-59, SOT-23, TO-236 (Pb-Free)	3,000 / Tape & Reel	
CPH3348-TL-W	WL.	CPH3 SC-59, SOT-23, TO-236 (Pb-Free / Halogen Free)	3,000 / Tape & Neel	

[†] For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. http://www.onsemi.com/pub_link/Collateral/BRD8011-D.PDF

Note on usage: Since the CPH3348 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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